General purpose (dual digital transistors) UMH2N / IMH2A

Features

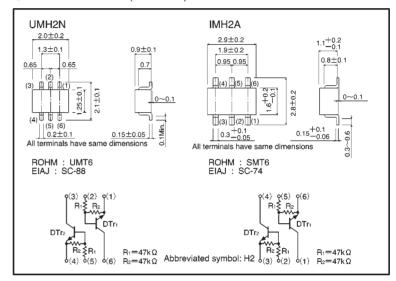
- Two DTC144Es chips in a UMT or SMT package.
- Mounting possible with UMT3 or SMT3 automatic mounting machines
- 3) Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.

Structure

Epitaxial planar type NPN silicon transistor (Built-in resistor type)

The following characteristics apply to both DTr₁ and DTr₂.

●External dimensions (Units: mm)



● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit	
Supply voltage		Vcc	50	V	
Input voltage		Vin	40	V	
		V 114	-10		
Output current		lo	lo 30		
		IC(Max.)	100	mA mA	
Power dissipation	UMH2N	Pd	150(TOTAL)	*1 mW	
	IMH2A	Fu	300 (TOTAL)	*2	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55~+150	°C	

^{*1 120}mW per element must not be exceeded.

^{*2 200}mW per element must not be exceeded.

Transistors UMH2N/IMH2A

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Input voltage	VI(off)	_	_	0.5	V	Vcc=5V, lo=100 μ A	
Input voltage	VI(on)	3	_	_	V	Vo=0.3V, Io=2mA	
Output voltage	V _{O(on)}	_	0.1	0.3	٧	Io/Ii=10mA/0.5mA	
Input current	lı	_	_	0.18	mA	V ₁ =5V	
Output current	IO(off)	_	_	0.5	μΑ	Vcc=50V, Vi=0V	
DC current gain	Gı	68	_	_	_	Vo=5V, Io=5mA	
Transition frequency	f⊤	_	250	_	MHz	Vc=10mA, I=-5mA, f=100MHz*	
Input resistance	Rı	32.9	47	61.1	kΩ	_	
Resistance ratio	R2/R1	0.8	1	1.2	_	_	

^{*} Transition frequency of the device

Packaging specifications

	Packaging type	Tap	ing
	Code		T110
Part No.	Basic ordering unit (pieces)	3000	3000
UMH2N		0	_
IMH2A		_	0

Electrical characteristic curves

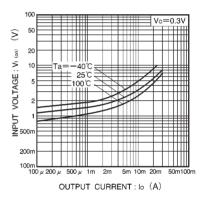


Fig.1 Input voltage vs. output current (ON characteristics)

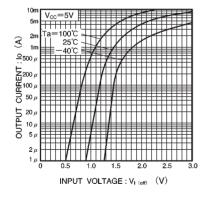


Fig.2 Output current vs. input voltage (OFF characteristics)

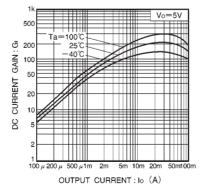


Fig.3 DC current gain vs. output current

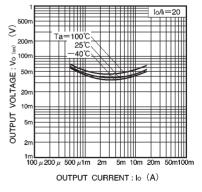


Fig.4 Output voltage vs. output current